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October 2013

FCH47N60F

N-Channel SuperFET® FRFET® MOSFET

600 V, 47 A, 73 m Ω

Features

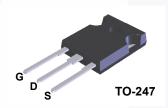
- 650 V @ T_{.I} = 150 °C
- Typ. R_{DS(on)} = 58 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 210 nC)
- Low Effective Output Capacitance (Typ. Cosseff. = 420 pF)
- · 100% Avalanche Tested
- RoHS Compliant

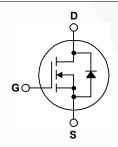
Applications

- Solar Inverter
- · AC-DC Power Supply

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server / telecom power, FPD TV power, ATX power and industrial power applications. SuperFET FRFET® MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FCH47N60F_F133	Unit	
V _{DSS}	Drain-Source Voltage		600	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$)		47 29.7	A A	
I _{DM}	Drain Current - Pulsed	(Note 1)	141	Α	
V _{GSS}	Gate-Source voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1800	mJ	
I _{AR}	Avalanche Current	(Note 1)	47	Α	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	41.7	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	50	V/ns	
P_{D}	Power Dissipation (T _C = 25°C) - Derate above 25°C				
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FCH47N60F_F133	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.3	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	41.7	°C/W	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCH47N60F	FCH47N60F_F133	TO-247	-	-	30

Electrical Characteristics $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Off Charac	cteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA, T _J = 25°C	600			V
	$V_{GS} = 0V$, $I_D = 250\mu A$, $T_J = 150^{\circ} C$		650		V	
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		0.6		V/°C
BV _{DS}	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0V$, $I_D = 47A$		700		V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600V, V _{GS} = 0V V _{DS} = 480V, T _C = 125°C			10 100	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V			-100	nA
On Charac	cteristics			•		
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 23.5A	-	0.062	0.073	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 23.5A	\	40		S
Dynamic C	Characteristics			•	•	
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz		5900	8000	pF
C _{oss}	Output Capacitance			3200	4200	pF
C _{rss}	Reverse Transfer Capacitance			250		pF
C _{oss}	Output Capacitance	V _{DS} = 480V, V _{GS} = 0V, f = 1.0MHz		160		pF
C _{oss} eff.	Effective Output Capacitance	V _{DS} = 0V to 400V, V _{GS} = 0V		420		pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 300V, I_{D} = 47A$ $R_{G} = 25\Omega$	/	185	430	ns
t _r	Turn-On Rise Time			210	450	ns
t _{d(off)}	Turn-Off Delay Time		/	520	1100	ns
t _f	Turn-Off Fall Time	(Note 4)		75	160	ns
Qg	Total Gate Charge	V _{DS} = 480V, I _D = 47A V _{GS} = 10V		210	270	nC
Q _{gs}	Gate-Source Charge			38	//	nC
Q _{gd}	Gate-Drain Charge	(Note 4)		110		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings			•	
I _S	Maximum Continuous Drain-Source Dio	de Forward Current			47	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	orward Current			141	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 47A			1.4	٧
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 47A		240		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100A/μs		2.04		μС

NOTES

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature

^{2.} I_{AS} = 18A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}C$

^{3.} $I_{SD} \le 47 \text{A}$, di/dt $\le 1200 \text{A}/\mu \text{s}$, $V_{DD} \le BV_{DSS}$, Starting T_J = 25°C

^{4.} Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

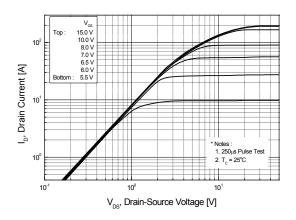


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

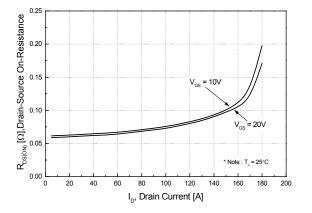


Figure 2. Transfer Characteristics

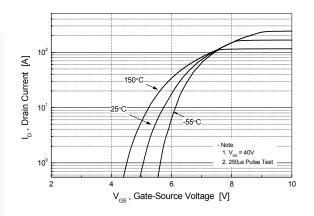


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

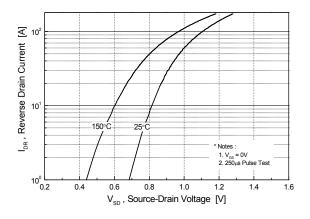


Figure 5. Capacitance Characteristics

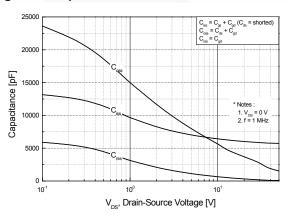
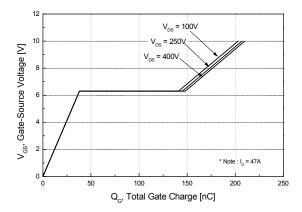


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

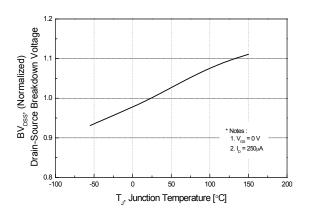


Figure 8. On-Resistance Variation vs. Temperature

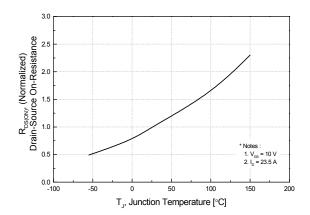


Figure 9. Safe Operating Area

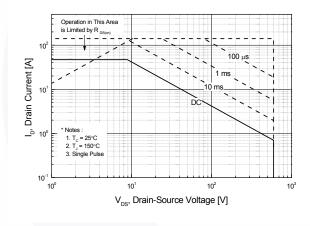


Figure 10. Maximum Drain Current vs. Case Temperature

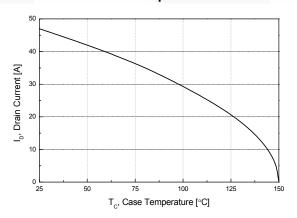


Figure 11. Transient Thermal Response Curve

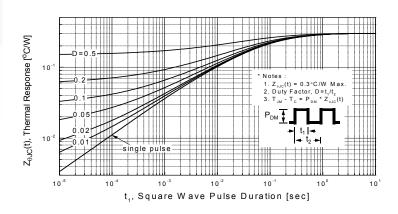


Figure 12. Gate Charge Test Circuit & Waveform

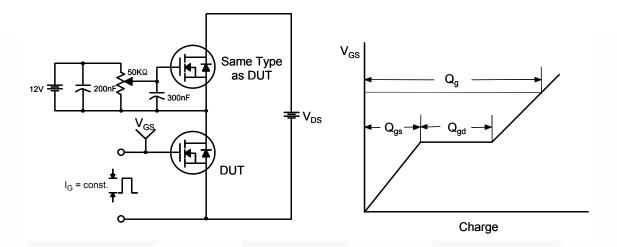


Figure 13. Resistive Switching Test Circuit & Waveforms

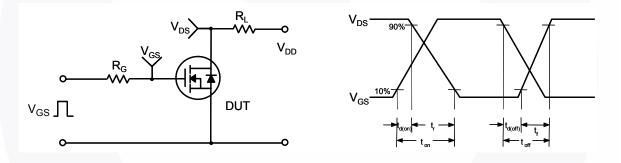
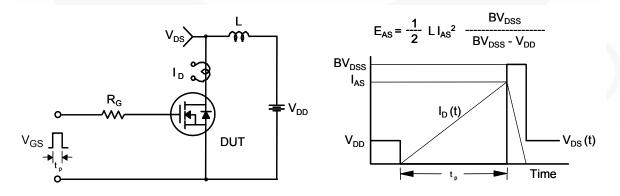


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



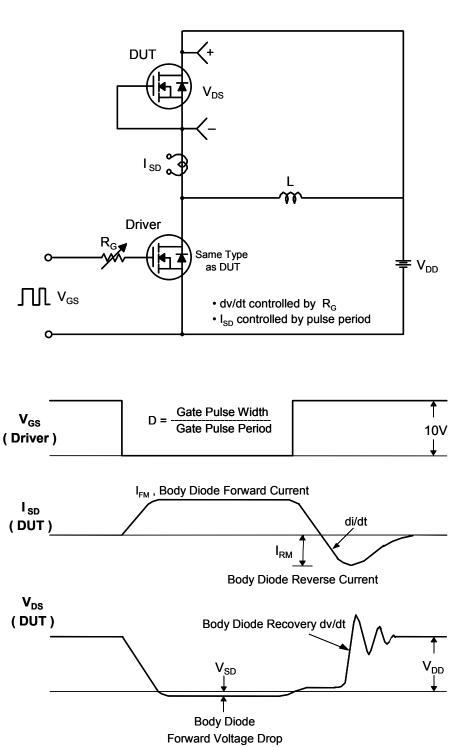
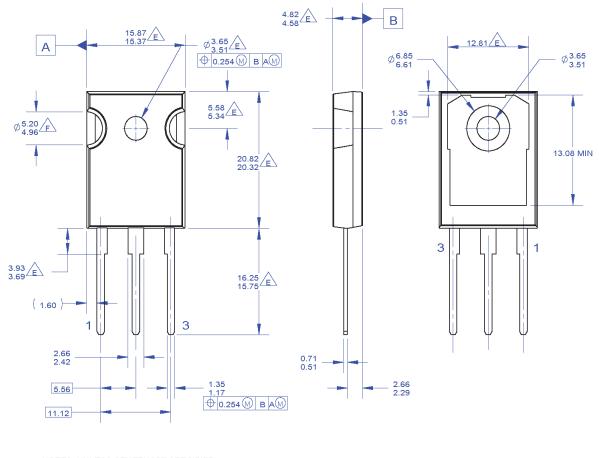


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

TO-247 3L



NOTES: UNLESS OTHERWISE SPECIFIED

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G. DRAWING FILENAME: MKT-TO247A03_REV03

Figure 16. TO-247, Molded, 3 Lead, Jedec Variation AB

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Dimension in Millimeters





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